

ABSTRACT OF THE DISCLOSURE

A metal CVD process includes a step (A) of introducing a gaseous source material containing a metal carbonyl compound into a process space adjacent to a surface of a substrate to be processed in such a manner that the metal carbonyl compound has a first partial pressure, and a step (B) of depositing a metal film on the surface of the substrate by introducing a gaseous source material containing the metal carbonyl compound into the process space in such a manner that the metal carbonyl compound has a second, smaller partial pressure. The step (A) is conducted such that there is caused no substantial deposition of the metal film on the substrate.

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